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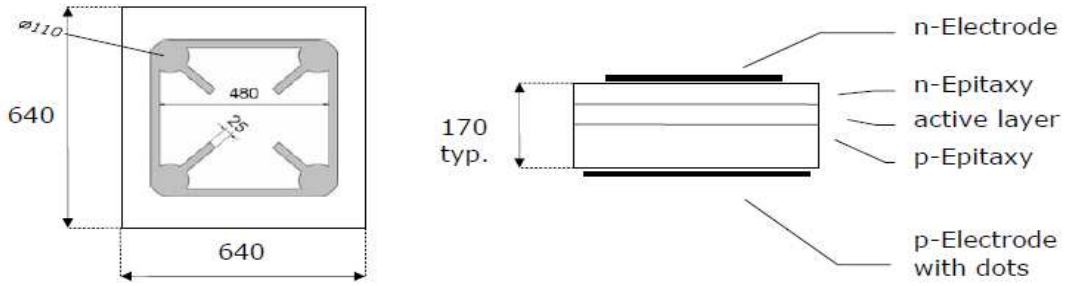
Data Sheet

LED Chip Infrared EOLC-880-22

Rev. 02, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, substrate removed	N (cathode) up, frame contact



chip thickness tolerance: ±50 µm p- and n-side electrodes: Au alloy

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=100 mA	V_F		1.35	1.6	V
Forward voltage	I_F=400 mA	V_F		1.8	1.9	V
Reverse current	V_R=5 V	I_R			100	µA
Radiant power*	I_F=20 mA	Φ_e	3	4.5		mW
Peak wavelength	I_F=100 mA	λ_p	870	880	890	nm
FWHM	I_F=20 mA	$\Delta\lambda_{0.5}$		40		nm
Switching time	I_F=100 mA	t_r, t_f		21; 15		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Chips fulfill the requirements of ROHS Directive 2011/65/EC "REACH-compliant"

Art. No. 131 148